

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5041	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/21 23:56
S1	151269	(semiconductor or die or chip or IC) and (transistor or mos) or ((silicon near carbide) or ("Si" near "C")) and (meta near carbide) same electrode	USPAT	OR	OFF	2004/12/21 13:09
S2	0	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (meta near carbide) same electrode	USPAT	OR	OFF	2004/12/21 13:09
S3	0	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (meta near carbide) and electrode	USPAT	OR	OFF	2004/12/21 13:09
S4	0	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (meta near carbide)	USPAT	OR	OFF	2004/12/21 13:10
S5	3283	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C"))	USPAT	OR	OFF	2004/12/21 13:10
S6	91	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and ((Ti" near "C") or titanium near carbide)	USPAT	OR	OFF	2004/12/21 13:25
S7	89	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" adj "C")) and ((Ti" adj "C") or titanium near carbide)	USPAT	OR	ON	2004/12/21 13:56
S8	3049	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and ((Ti" near "C") or titanium near carbide or metal near carbides or conductive carbides)	USPAT	OR	ON	2004/12/21 13:57

S9	171	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and ((("Ti" near "C") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:28
S10	182	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:31
S11	17	S10 not S9	USPAT	OR	ON	2004/12/21 14:29
S12	16	257/758 and ((silicon near carbide) or ("SiC")) with (film or layer) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:32
S13	22	257/758 and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:24
S14	3295	(semiconductor or die or chip or Ic) and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:59
S15	1050	(semiconductor or die or chip or Ic) and ((silicon near carbide) or ("SiC")) with (layer or film) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:22
S16	505	S15 and ((silicon near carbide) or ("SiC")) with (layer or film) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides) and electrode	USPAT	OR	ON	2004/12/21 15:43
S17	545	S15 not S16	USPAT	OR	ON	2004/12/21 15:43
S18	34	(semiconductor or die or chip or Ic) and ((silicon near carbide) or ("SiC")) with (layer or film) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	JPO	OR	ON	2004/12/21 16:22

S19	15	257/750 and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:26
S20	12	257/763 and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:26
S21	14	257/763 and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides or "TaC")	USPAT; JPO	OR	ON	2004/12/21 17:56
S22	3499	(semiconductor or die or chip or IC) and ((silicon near carbide) or ("SiC")) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides or "TaC")	USPAT; JPO	OR	ON	2004/12/21 16:29
S23	1958	S22 and (gate or source or drain)	USPAT; JPO	OR	ON	2004/12/21 16:29
S24	1213	(semiconductor or die or chip or IC) and ((silicon near carbide) or ("SiC")) with (insulat\$3 or dielectric or film or layer) and ((("TiC") or titanium near carbide or metal near carbides or conductive near carbides or "TaC")	USPAT; JPO	OR	ON	2004/12/21 16:29
S25	788	S24 and (gate or source or drain)	USPAT; JPO	OR	ON	2004/12/21 17:14
S26	1	"09252095"	JPO	OR	ON	2004/12/21 17:14
S27	515	(transistor or MOS or FET) and (semiconductor or die or chip or IC) and ((silicon near carbide) or ("SiC")) with (film or layer) and ((("TiC") or (titanium or zirconium or hafnium or vanadium or niobium or tantalum) near carbide or "TaC")	USPAT; JPO	OR	ON	2004/12/21 18:01
S28	2967	257/774	USPAT	OR	OFF	2004/12/21 19:39
S29	3612	257/774	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/21 19:39